

FQU5N60CTU

FQU5N60CTU Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



FQU5N60CTU Specifications

Manufacturer Part NumberFQU5N60CTUManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-251-3 Short Leads, IPak, TO-251AASeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs5.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs5.5W (Ta), 49W (Tc)Mounting TypeIhrough HoleSupplier Device PackageIhrough HoleSupplier Device PackageIhrough Hole		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-251-3 Short Leads, IPak, TO-251AASeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds570F @ 25VYgs (Max)1.90VFET Feature-Power Dissipation (Max)2.50 (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.50 hm @ 1.4A, 10VOperating TemperatureF5°C ~ 150°C (TJ)Mounting TypeIPakaPackage / CaseTo-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	FQU5N60CTU
Transistors - FETs, MOSFETs - SinglePackageTO-251-3 Short Leads, IPak, TO-251AASeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPakPackage / CaseTO-251.3 Short Leads, IPak, TO-251AA	Manufacturer	Fairchild/ON Semiconductor
PackageTO-251-3 Short Leads, IPak, TO-251AASeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds670pF @ 25VInput Capacitance (Ciss) (Max) @ Vds570pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs5.5° C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPAkPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs5.5° C ~ 150° C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5V (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C2.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageIPakPackage / CaseTO-251.3 Short Leads, IPak, TO-251AA	Series	QFET?
Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 2.8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Iput Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5 W(Ta), 49W (Tc) Rds On (Max) @ Id, Vgs 2.5 Ohm @ 1.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Paak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°С 2.8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Ta), 49W (Tc) Rds On (Max) @ Id, Vgs 2.5 Ohm @ 1.4A, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package IPaka Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Ta), 49W (Tc) Rds On (Max) @ Id, Vgs 2.5 Ohm @ 1.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package IPAk Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Current - Continuous Drain (Id) @ 25°C	2.8A (Tc)
Gate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250µA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	19nC @ 10V
FET Feature-Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	670pF @ 25V
Power Dissipation (Max)2.5W (Ta), 49W (Tc)Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs2.5 Ohm @ 1.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	2.5W (Ta), 49W (Tc)
Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	2.5 Ohm @ 1.4A, 10V
Supplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Papert arrers?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
kepolt enois:		Report errors?

FQU5N60CTU Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

FQU5N60CTU Payment Methods



FQU5N60CTU Shipping Methods



If you have any question about FQU5N60CTU, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com